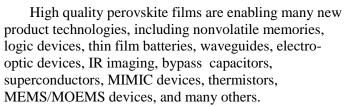
Perovskite Complex Oxide Films by $SpinCVD^{TM}$

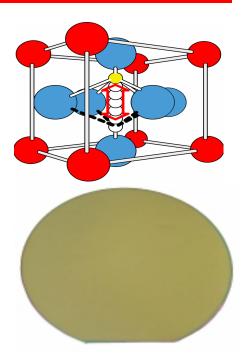
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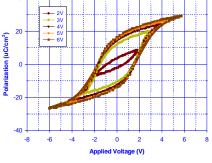
The SMI *SpinCVD*TM deposition system is ideally suited for depositing perovskite layers of uniform thickness and composition. The perovskite structure shown at right consists of an ABO₃ crystal lattice. Perovskites have a variety of properties important to ferroelectric, pyroelectric, piezoelectric, optical, conductive, superconductor and dielectric applications. Repeatable deposition of ABO₃ films is routinely accomplished using the SMI *SpinCVD*TM deposition system. Shown at the right is a perovskite film on a 6" silicon wafer with better than 1% uniformity. SpinCVDTM films allow device development with confident and predictable performance. An example is the ferroelectric hysteresis shown below, which is critical to production of non-volatile memory devices. A cross-sectional SEM of an integrated memory cell using ferroelectric switching PZT is also shown.

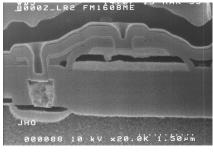


The versatility of SMI's *SpinCVD*TM system allows production of multi-layer thin film stacks for applications such as optical interference filters. SMI *SpinCVD*TM systems are available to produce perovskites for either research or production- making the transition of new material systems into manufacturing very straightforward.

High quality perovskite films are easily deposited by SMI $SpinCVD^{TM}$ deposition systems. Oxide films deposited by $SpinCVD^{TM}$ include: PZT, SBT, BST, CMO, YBCO, ZnO, Al₂O₃, HfO₂, LiNbO₃, SiO₂, ZrO₂, Ta₂O₅, among many others.









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